

# 2SJ479(L), 2SJ479(S)

Silicon P Channel DV-L MOS FET  
High Speed Power Switching

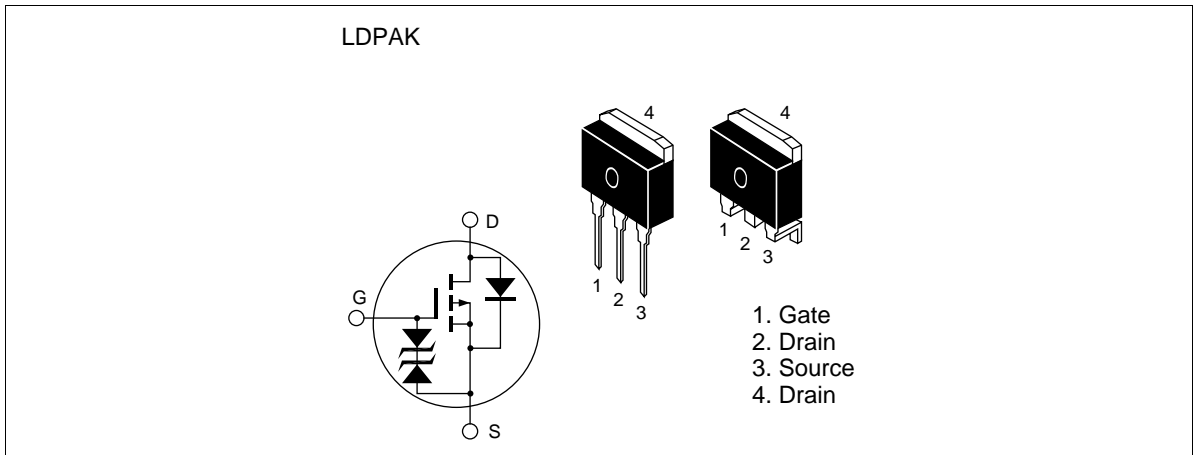
# HITACHI

ADE-208-541  
1st. Edition

## Features

- Low on-resistance  
 $R_{DS(on)} = 25 \text{ m}\Omega$  typ.
- 4V gate drive devices.
- High speed switching

## Outline



## 2SJ479(L), 2SJ479(S)

### Absolute Maximum Ratings (Ta = 25°C)

Item	Symbol	Ratings	Unit
Drain to source voltage	V <sub>DSS</sub>	-30	V
Gate to source voltage	V <sub>GSS</sub>	±20	V
Drain current	I <sub>D</sub>	-30	A
Drain peak current	I <sub>D(pulse)</sub> <sup>Note1</sup>	-120	A
Body to drain diode reverse drain current	I <sub>DR</sub>	-30	A
Channel dissipation	Pch <sup>Note2</sup>	50	W
Channel temperature	Tch	150	°C
Storage temperature	Tstg	-55 to +150	°C

Notes: 1. PW ≤ 10μs, duty cycle ≤ 1 %

2. Value at Tc = 25°C

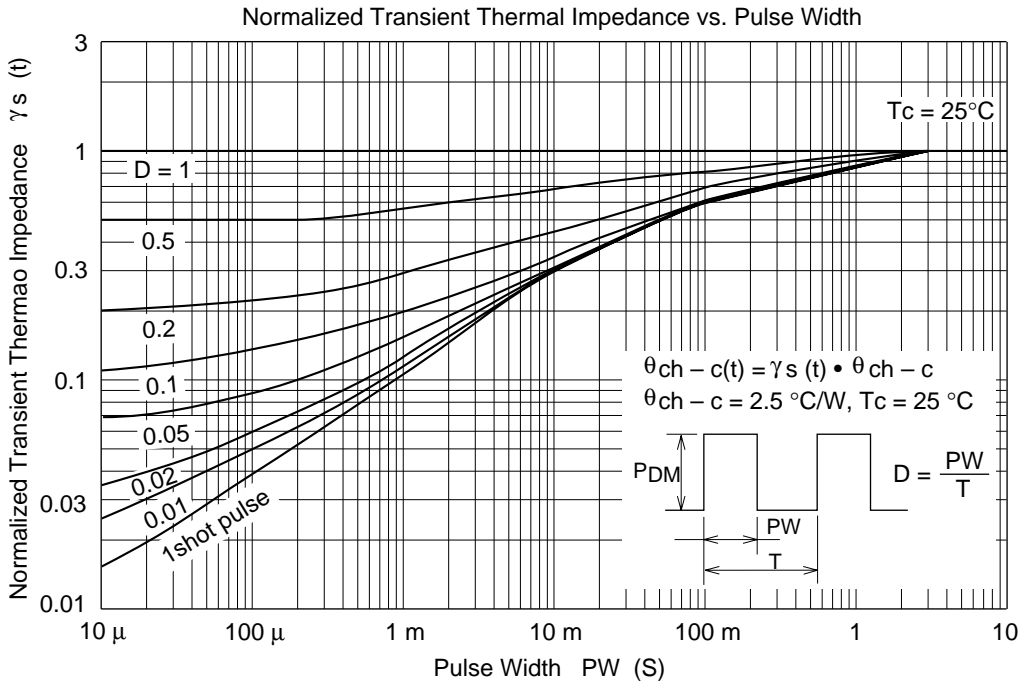
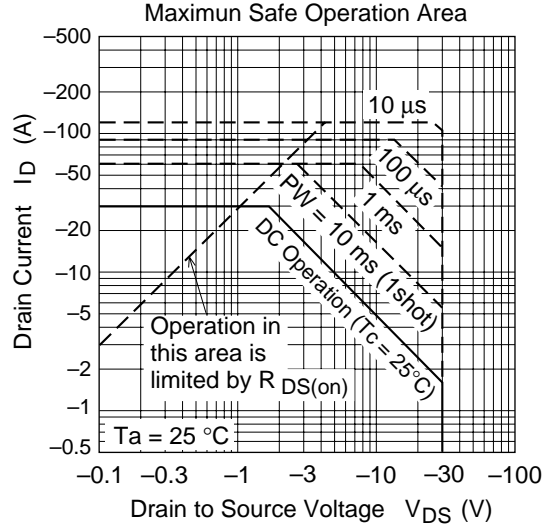
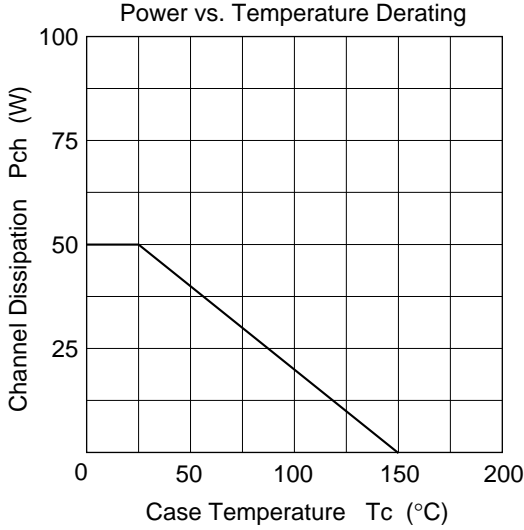
**Electrical Characteristics (Ta = 25°C)**

Item	Symbol	Min	Typ	Max	Unit	Test Conditions
Drain to source breakdown voltage	$V_{(BR)DSS}$	-30	—	—	V	$I_D = -10\text{mA}$ , $V_{GS} = 0$
Gate to source breakdown voltage	$V_{(BR)GSS}$	±20	—	—	V	$I_G = \pm 100\mu\text{A}$ , $V_{DS} = 0$
Zero gate voltage drain current	$I_{DSS}$	—	—	-10	μA	$V_{DS} = -30\text{V}$ , $V_{GS} = 0$
Gate to source leak current	$I_{GSS}$	—	—	±10	μA	$V_{GS} = \pm 16\text{V}$ , $V_{DS} = 0$
Gate to source cutoff voltage	$V_{GS(off)}$	-1.0	—	-2.0	V	$I_D = -1\text{mA}$ , $V_{DS} = -10\text{V}$
Static drain to source on state resistance	$R_{DS(on)}$	—	25	35	mΩ	$I_D = -15\text{A}$ , $V_{GS} = -10\text{V}$ <sup>Note3</sup>
	$R_{DS(on)}$	—	40	60	mΩ	$I_D = -15\text{A}$ , $V_{GS} = -4\text{V}$ <sup>Note3</sup>
Forward transfer admittance	$ y_{fs} $	12	20	—	S	$I_D = -15\text{A}$ , $V_{DS} = -10\text{V}$ <sup>Note3</sup>
Input capacitance	$C_{iss}$	—	1700	—	pF	$V_{DS} = -10\text{V}$
Output capacitance	$C_{oss}$	—	950	—	pF	$V_{GS} = 0$
Reverse transfer capacitance	$C_{rss}$	—	260	—	pF	$f = 1\text{MHz}$
Turn-on delay time	$t_{d(on)}$	—	20	—	ns	$V_{GS} = -10\text{V}$ , $I_D = -15\text{A}$
Rise time	$t_r$	—	290	—	ns	$R_L = 0.67\Omega$
Turn-off delay time	$t_{d(off)}$	—	170	—	ns	
Fall time	$t_f$	—	130	—	ns	
Body to drain diode forward voltage	$V_{DF}$	—	-1.1	—	V	$I_F = -30\text{A}$ , $V_{GS} = 0$
Body to drain diode reverse recovery time	$t_{rr}$	—	70	—	ns	$I_F = -30\text{A}$ , $V_{GS} = 0$ $diF/dt = 50\text{A}/\mu\text{s}$

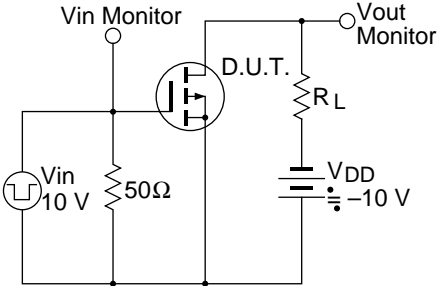
Note: 3. Pulse test

See characteristic curves of 2SJ471

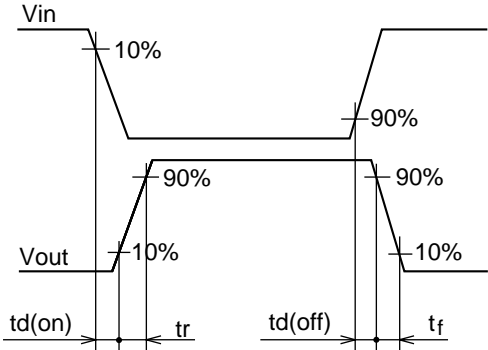
Main Characteristics



Switching Timen Test Circuit



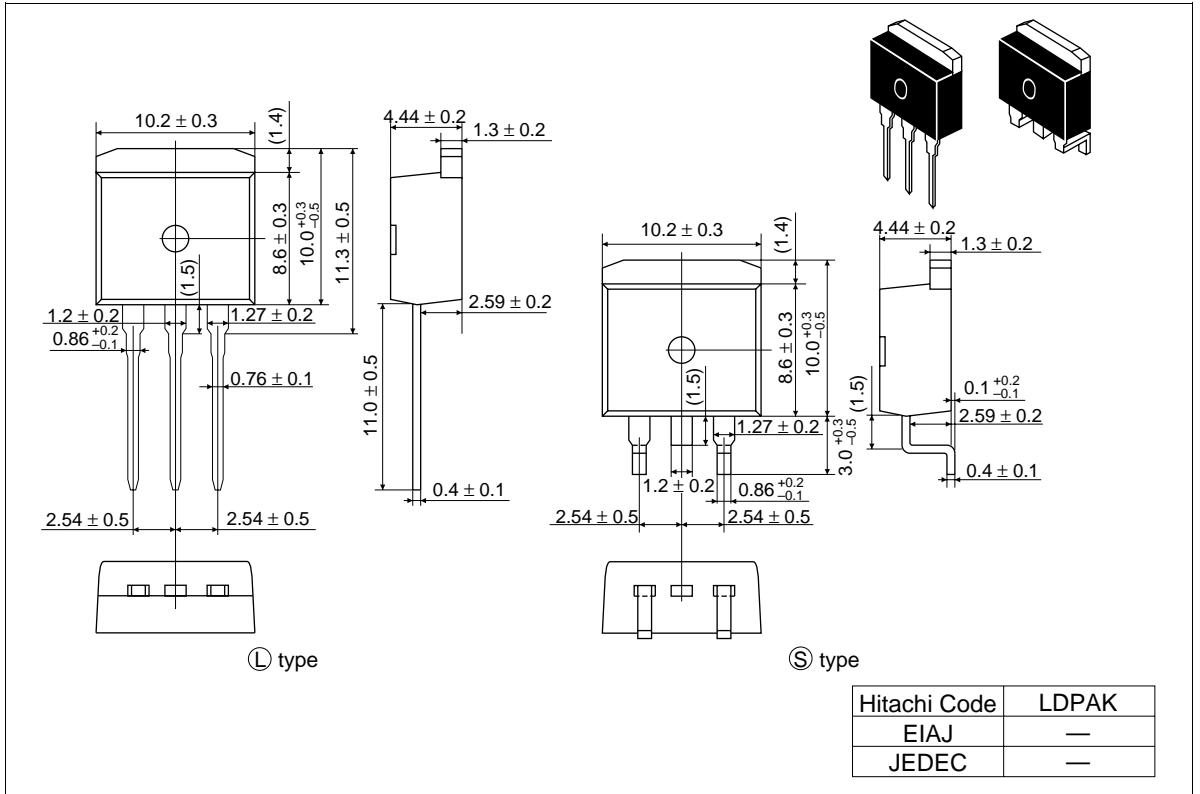
Waveform



# 2SJ479(L), 2SJ479(S)

## Package Dimensions

Unit: mm



## Cautions

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